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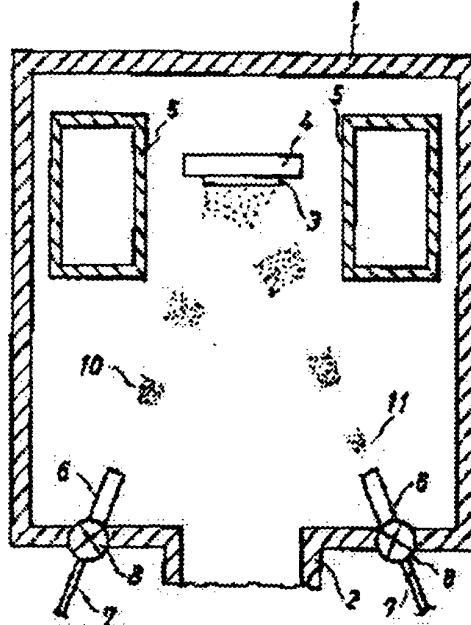
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(54) FILM FORMATION METHOD AND FILM FORMATION APPARATUS

(57)Abstract:

PURPOSE: To make it possible to form a thin film having an excellent in-plane uniformity, ALE condition, crystal quality, acute steepness of heterointerface, and others without damaging a substrate.

CONSTITUTION: A substrate 3 is arranged in a vacuum chamber 1 which is evacuated at a given degree of vacuum and heated. At the same time, with a gas ejection mechanism having a nozzle 6 arranged toward the substrate 3, and a high-speed switching valve 8 which provided near the nozzle 6, a material gas is ejected to the substrate 3 intermittently or continuously to grow crystals on the surface of the substrate 3 for the formation of a film.



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